

Form PTO-1449		U.S. Department of Commerce Patent and Trademark Office							Atty. Docket No. 2271/62289-Z	Serial No. 10/601, Not Yet Assigned 301
INFORMATION DISCLOSURE CITATION BY APPLICANT (Use several sheets if necessary)									Applicant Seiji SARAYAMA et al.	
									Filing Date	Group 2818
U.S. PATENT DOCUMENTS										
Examiner Initial		Document Number			Date	Name	Class	Subclass	Filing Date if Appropriate	
TP	AA	6	2	7	0	5	6	9	08/2001	Shibata et al.
TP	AB	6	1	7	7	0	5	7	01/2001	Purdy
TP	AC	5	8	6	8	8	3	7	02/1999	DiSalvo et al.
	AD									
	AE									
	AF									
	AG									
FOREIGN PATENT DOCUMENTS										
		Document Number			Date	Country	Class	Subclass	Translation	
									Yes	No
	AH									
	AI									
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)										
TP	AJ	"Preparation of GaN Single Crystals Using a Na Flux", H. Yamane et al., Chemical Mater., 1997, Vol. 9, No. 2, pp. 413-416.								
TP	AK	"InGaN/GaN/AlGaN-Based Laser Diodes With Cleaved Facets Grown on GaN Substrates", S. Nakamura et al., Applied Physics Letters, 1998, Vol. 73, No. 6, pp. 832-834.								
TP	AL	"Bulk and Homoepitaxial GaN-growth and Characterization", S. Porowski, Journal of Crystal Growth, 1998, Vol. 189/190, pp. 153-158.								
TP	AM	"InGaN/GaN/AlGaN-Based Laser Diodes With Modulation-Doped Strained-Layer Superlattices", S. Nakamura et al., Japanese Journal of Applied Physics, 1997, Vol. 36, No. 12A, pp. 1568-1571.								
	AN									
EXAMINER	T. Reho			DATE CONSIDERED		Feb, 2005				
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609: Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.										